

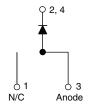
RoHS

HALOGEN

FREE

HEXFRED®, Ultrafast Soft Recovery Diode, 4 A





PRIMARY CHARACTERISTICS						
I _{F(AV)} 4 A						
V_{R}	600 V					
V _F at I _F	1.4 V					
t _{rr} typ.	17 ns					
T _J max.	150 °C					
Package DPAK (TO-252AA)						
Circuit configuration	Single					

FEATURES



- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Guaranteed avalanche
- · Specified at operating temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>



- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI / RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V _{RRM}		600	V			
Maximum continuous forward current	I _{F(AV)}	T _C = 100 °C	4				
Single pulse forward current	I _{FSM}		25	Α			
Repetitive peak forward current	I _{FRM}	T _C = 116 °C	16				
Maximum power dissipation	P _D	T _C = 100 °C	10	W			
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +150	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-		
Forward voltage See fig. 1		I _F = 4 A	-	1.5	1.8	V	
	V_{F}	I _F = 8 A	-	1.8	2.2		
See lig. 1		I _F = 4 A, T _J = 125 °C	-	1.4	1.7		
Maximum reverse		V _R = V _R rated	-	0.17	3.0		
leakage current	I _R	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	-	44	300	μA	
Junction capacitance	C _T	V _R = 200 V	-	4	8	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	





DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
		I _F = 1.0 A, dI _F /dt = 200 A/μA, V _R = 30 V		-	17	-		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	28	42	ns	
		T _J = 125 °C		-	38	57		
Dools recovery average	I _{RRM}	I _{RRM}	T _J = 25 °C	$I_F = 4 \text{ A}$	-	2.9	5.2	^
Peak recovery current			T _J = 125 °C		-	3.7	6.7	А
Poverse recovery charge	0	T _J = 25 °C	dl _F /dt = 200 A/μs V _B = 200 V	-	40	60	nC	
Reverse recovery charge	Q _{rr}	Q _{rr}	T _J = 125 °C		-	70	105	IIC IIC
Rate of fall of recovery current	dI _{(rec)M} /dt	-II /-II	T _J = 25 °C		-	280	-	Λ/μο
		T _J = 125 °C		-	235	-	A/µs	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	150	°C
Thermal resistance, junction to case	R _{thJC}		-	-	5.0	°C/W
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	- C/VV
Weight			-	2.0	-	g
vveigni			=	0.07	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style DPAK (TO-252AA)	HFA04SD60S			



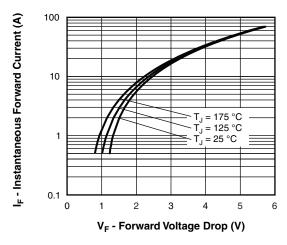


Fig. 1 - Typical Forward Voltage Drop Characteristics

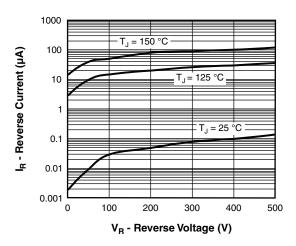


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

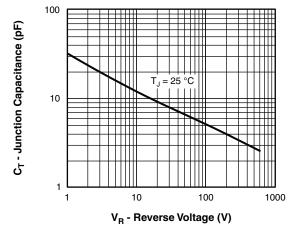


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

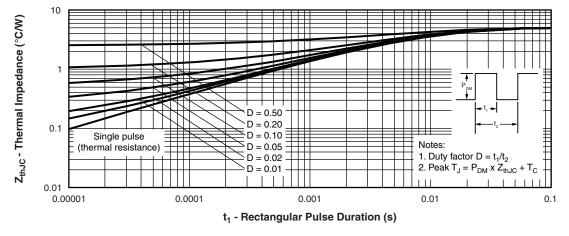


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

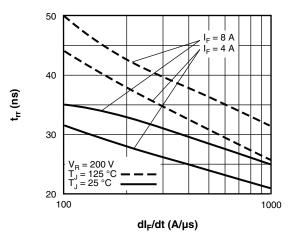


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

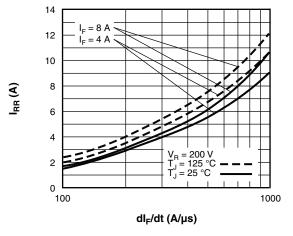


Fig. 6 - Typical Recovery Current vs. dl_F/dt

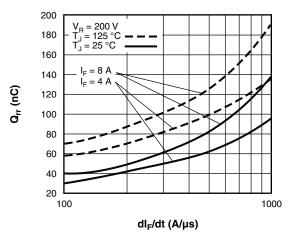


Fig. 7 - Typical Stored Charge vs. dl_F/dt

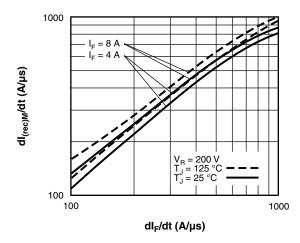


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

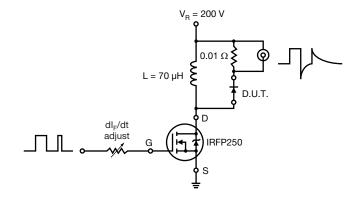
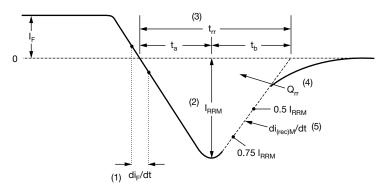


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

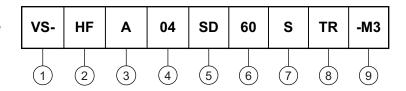
(5) $di_{(rec)M}/dt$ - peak rate of change of current during $t_{\rm b}$ portion of $t_{\rm rr}$

Fig. 10 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

3 - Electron irradiated

Current rating (04 = 4 A)

5 - D-PAK

6 - Voltage rating (60 = 600 V)

7 - S = D-PAK

8 - • TR = tape and reel

• R = tape and reel (right oriented)

• L = tape and reel (left oriented)

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-HFA04SD60S-M3	75	Antistatic plastic tube				
VS-HFA04SD60STR-M3	2000	13" diameter reel				
VS-HFA04SD60SL-M3	3000	13" diameter reel				
VS-HFA04SD60SR-M3	3000	13" diameter reel				

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95627</u>					
Part marking information	www.vishay.com/doc?95176				
Packaging information	www.vishay.com/doc?95033				



D-PAK (TO-252AA) "M"

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	2.18	2.39	0.086	0.094	
A1	-	0.13	-	0.005	
b	0.64	0.89	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	3
С	0.46	0.61	0.018	0.024	
c2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	5
D1	5.21	-	0.205	1	3
Е	6.35	6.73	0.250	0.265	5
E1	4.32	-	0.170	-	3

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STINIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
е	2.29	2.29 BSC		0.090 BSC	
Н	9.40	10.41	0.370	0.410	
L	1.40	1.78	0.055	0.070	
L1	2.74 BSC		0.108 REF.		
L2	0.51 BSC		0.020	BSC	
L3	0.89	1.27	0.035	0.050	3
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	2
Ø	0°	10°	0°	10°	
Ø1	0°	15°	0°	15°	
Ø2	25°	35°	25°	35°	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension uncontrolled in L5
- (3) Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- (5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (6) Dimension b1 and c1 applied to base metal only
- (7) Datum A and B to be determined at datum plane H
- (8) Outline conforms to JEDEC® outline TO-252AA



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